

# SILICON TRANSISTOR 2SB1453

## PNP SILICON EPITAXIAL POWER TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SB1453 is a power transistor that can directly drive from the IC output. This transistor is ideal for motor drivers and solenoid drivers in such as OA and FA equipment.

In addition, a small resin-molded insulation type package contributes to high-density mounting and reduction of mounting cost.

#### **FEATURES**

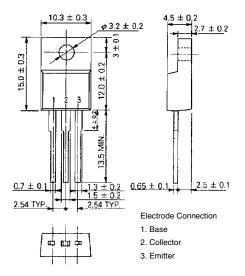
- High DC current amplifier ratio
   hFE ≥ 100 (VcE = -5 V, Ic = -0.5 A)
- Mold package that does not require an insulating board or insulation bushing

#### ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

| Parameter                    | Symbol             | Ratings     | Unit |
|------------------------------|--------------------|-------------|------|
| Collector to base voltage    | V <sub>СВО</sub>   | -60         | V    |
| Collector to emitter voltage | VCEO               | -60         | V    |
| Emitter to base voltage      | V <sub>EBO</sub>   | -7.0        | V    |
| Collector current (DC)       | Ic(DC)             | -3.0        | Α    |
| Collector current (pulse)    | Ic(pulse)*         | -6.0        | Α    |
| Base current (DC)            | I <sub>B(DC)</sub> | -1.0        | Α    |
| Total power dissipation      | P⊤ (Tc = 25°C)     | 25          | W    |
| Total power dissipation      | P⊤ (Ta = 25°C)     | 2.0         | W    |
| Junction temperature         | Tj                 | 150         | °C   |
| Storage temperature          | Tstg               | -55 to +150 | °C   |

<sup>\*</sup> PW  $\leq$  10 ms, duty cycle  $\leq$  50%

#### PACKAGE DRAWING (UNIT: mm)



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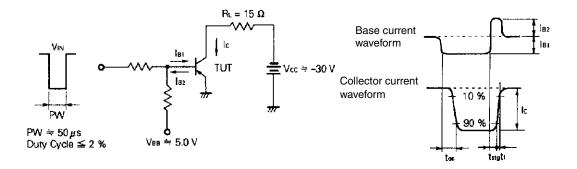


### **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

| Parameter                    | Symbol                  | Conditions   | MIN. | TYP. | MAX. | Unit |
|------------------------------|-------------------------|--|------|------|------|------|
| Collector cutoff current     | Ісво                    | $V_{CB} = -60 \text{ V}, I_E = 0$  |      |      | -10  | μΑ   |
| DC current gain              | h <sub>FE1</sub> **     | $V_{CE} = -5.0 \text{ V}, \text{ Ic} = -0.5 \text{ A}$                         | 100  |      | 400  | -    |
| DC current gain              | h <sub>FE2</sub> **     | $V_{CE} = -5 \text{ V}, \text{ Ic} = -3 \text{ A}$                             | 20   |      |      | -    |
| Collector saturation voltage | V <sub>CE(sat)</sub> ** | Ic = -3.0  A, IB = -300  mA  |      |      | -1.0 | V    |
| Base saturation voltage      | V <sub>BE(sat)</sub> ** | Ic = -3.0  A, IB = -300  mA  |      |      | -2.0 | V    |
| Gain bandwidth product       | f⊤                      | $V_{CE} = -5.0 \text{ V}, \text{ Ic} = -0.5 \text{ A}$                         |      | 5    |      | MHz  |
| Collector capacitance        | Cob                     | $V_{CB} = -10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$                         |      | 80   |      | pF   |
| Turn-on time                 | ton                     | $I_C = -2.0 \text{ A}, I_{B1} = -I_{B2} = -200 \text{ mA},$                    |      | 0.4  |      | μs   |
| Storage time                 | tstg                    | R <sub>L</sub> = 15 $\Omega$ , Vcc $\cong$ -30 V<br>Refer to the test circuit. |      | 1.7  |      | μs   |
| Fall time                    | tf                      |  |      | 0.5  |      | μs   |

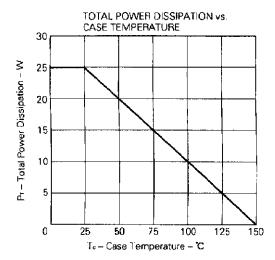
<sup>\*\*</sup> Pulse test PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2%

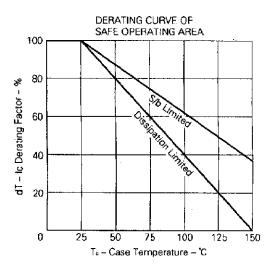
### SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT

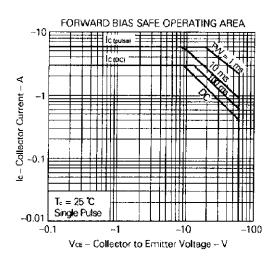


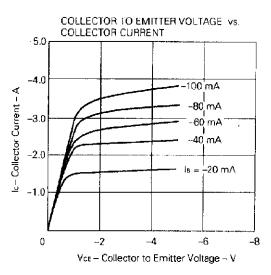


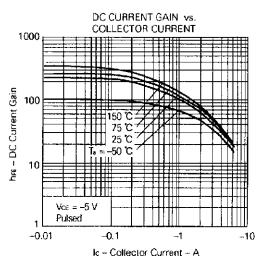
#### TYPICAL CHARACTERISTICS (Ta = 25°C)

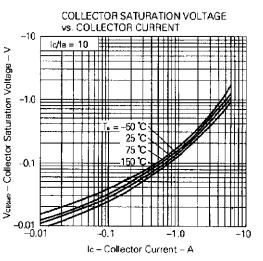




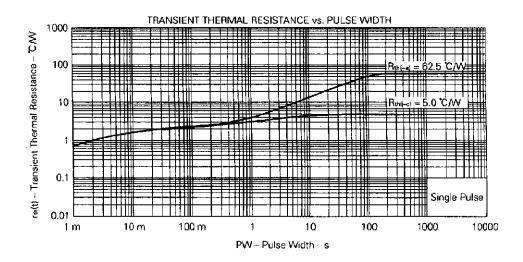


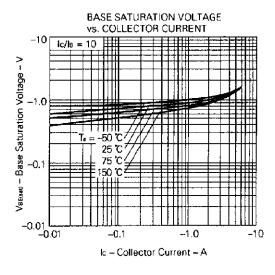


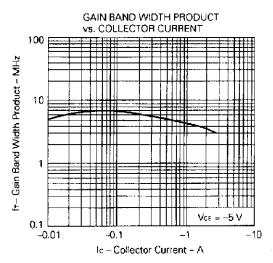


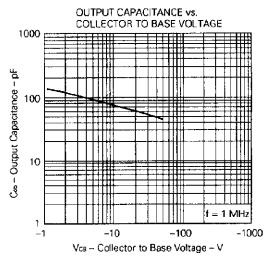


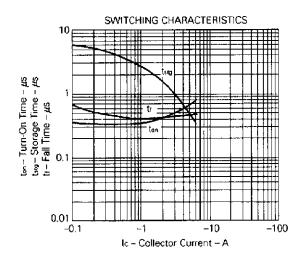
Data Sheet D16129EJ2V0DS 3













[MEMO]

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